NTTFS4824N

[MOSFET](#) – Power, Single, N-Channel, µ8FL
30 V, 69 A

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC−DC Converters
- Low Side Switching

ON Semiconductor®

http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	5.0 mΩ @ 10 V	69 A
	7.5 mΩ @ 4.5 V	

N−Channel MOSFET

D (5−8)

G (4)

S (1,2,3)

WDFN8 (µ8FL) CASE 511AB FLAT LEAD

MARKING DIAGRAM


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S        D
S  4824  D
S  AYWW■ D
G    ■   
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4824 = Specific Device Code
A   = Assembly Location
Y   = Year
WW   = Work Week
■   = Pb−Free Package

(Note: Microdot may be in either location)

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{θJA}$ (Note 1)	Steady State	T_A = 25°C	I_D	14.9	A
		T_A = 85°C		10.8	
Power Dissipation $R_{θJA}$ (Note 1)		T_A = 25°C	P_D	2.2	W
Continuous Drain Current $R_{θJA}$ ≤ 10 s (Note 1)		T_A = 25°C	I_D	20.6	A
		T_A = 85°C		14.9	
Power Dissipation $R_{θJA}$ ≤ 10 s (Note 1)		T_A = 25°C	P_D	4.1	W
Continuous Drain Current $R_{θJA}$ (Note 2)		T_C = 25°C	I_D	8.3	A
		T_C = 85°C		6.0	
Power Dissipation $R_{θJA}$ (Note 2)		T_C = 25°C	P_D	0.66	W
Continuous Drain Current $R_{θJC}$ (Note 1)		T_C = 25°C	I_D	69	A
		T_C = 85°C		50	
Power Dissipation $R_{θJC}$ (Note 1)		T_C = 25°C	P_D	46.3	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 µs		I_{DM}	207	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to +150	°C
Source Current (Body Diode)			I_S	46.3	A
Drain to Source dV/dt			dV/dt	6.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{DD} = 50 V, V_{GS} = 10 V, I_L = 38 A_{pk}, L = 0.1 mH, R_G = 25 Ω)			E_{AS}	72	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
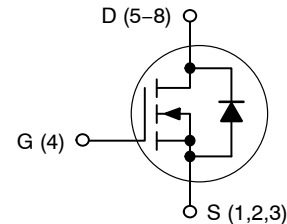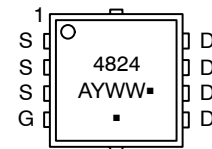1. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.

ORDERING INFORMATION

Device	Package	Shipping[†]
NTTFS4824NTAG	WDFN8 (Pb−Free)	1500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

2. Surface−mounted on FR4 board using the minimum recommended pad size.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	2.7	°C/W
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	57.7	
Junction−to−Ambient − Steady State (Note 4)	$R_{\theta JA}$	187.8	
Junction−to−Ambient − (t ≤ 10 s) (Note 3)	$R_{\theta JA}$	30.3	

3. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
4. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				25		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5	1.9	2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				6		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V to 11.5 V	I_D = 20 A		3.7	5.0	mΩ
			I_D = 10 A		3.6		
		V_{GS} = 4.5 V	I_D = 20 A		5.8	7.5	
			I_D = 10 A		5.7		
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 20 A			53		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 12 V			1750	2363	pF
Output Capacitance	C_{oss}				350	473	
Reverse Transfer Capacitance	C_{rss}				170	255	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 20 A			12.6	18	nC
Threshold Gate Charge	$Q_{G(TH)}$				1.7		
Gate−to−Source Charge	Q_{GS}				4.7		
Gate−to−Drain Charge	Q_{GD}				4.8		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 11.5 V, V_{DS} = 15 V, I_D = 20 A			29		nC
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			13		ns
Rise Time	t_r				38		
Turn−Off Delay Time	$t_{d(off)}$				18		
Fall Time	t_f				5.5		

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

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**ELECTRICAL CHARACTERISTICS** (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 11.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			9.0		ns
Rise Time	t_r				21		
Turn−Off Delay Time	$t_{d(off)}$				25		
Fall Time	t_f				4.4		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 20 A	T_J = 25°C		0.8	1.0	V
			T_J = 125°C		0.7		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = 20 A			22		ns
Charge Time	t_a				10.5		
Discharge Time	t_b				11.5		
Reverse Recovery Charge	Q_{RR}				10		nC
PACKAGE PARASITIC VALUES							
Source Inductance	L_S	T_A = 25°C			0.38		nH
Drain Inductance	L_D				0.054		
Gate Inductance	L_G				1.3		
Gate Resistance	R_G				0.9	2.0	Ω

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

Figure 1. On−Region Characteristics
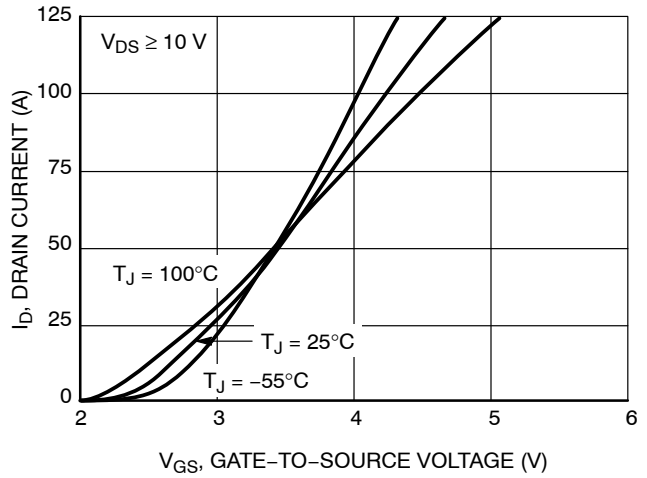
Figure 2. Transfer Characteristics
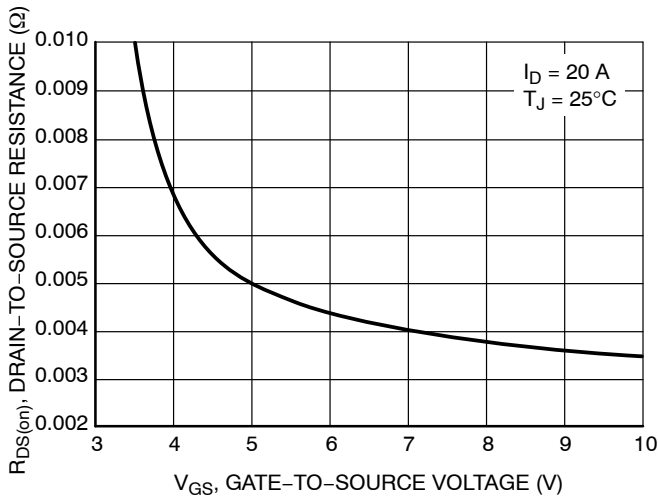
Figure 3. On−Resistance vs. Gate−to−Source Voltage
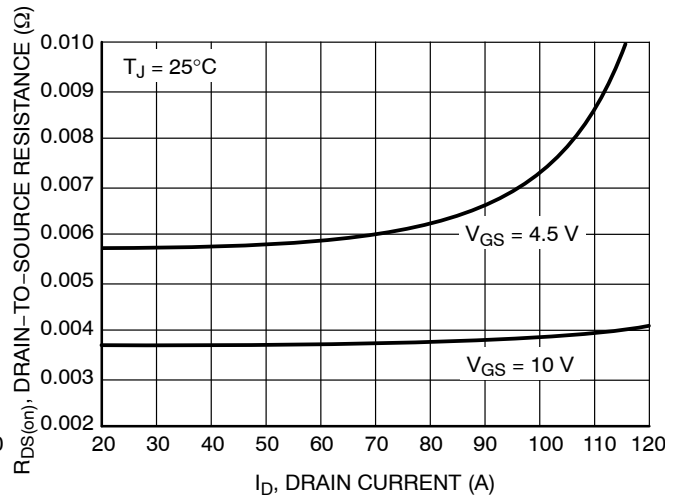
Figure 4. On−Resistance vs. Drain Current and Gate Voltage
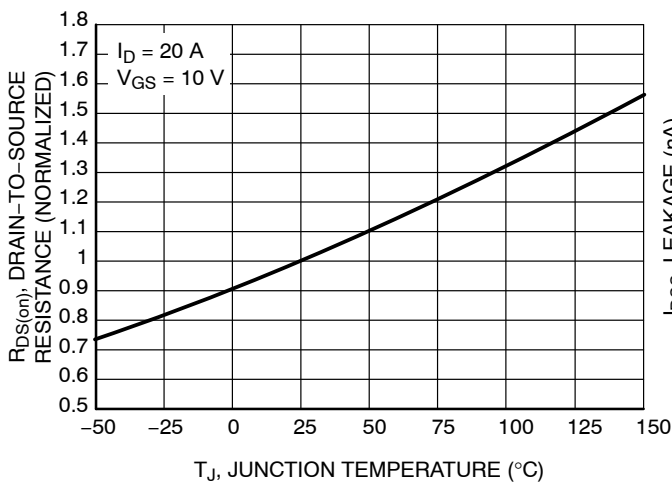
Figure 5. On−Resistance Variation with Temperature
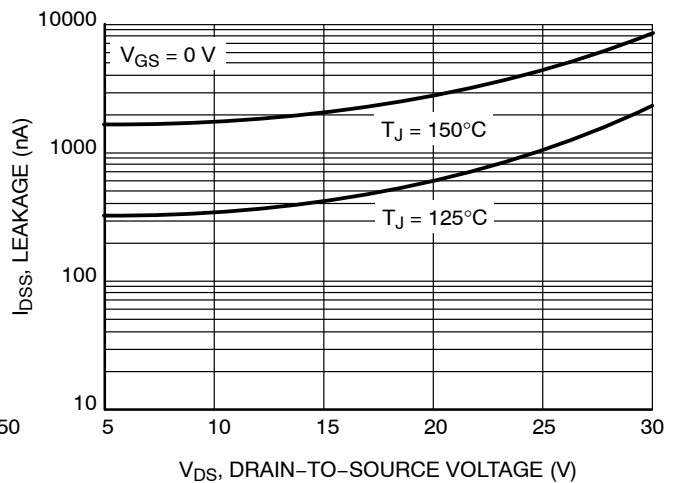
Figure 6. Drain−to−Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS
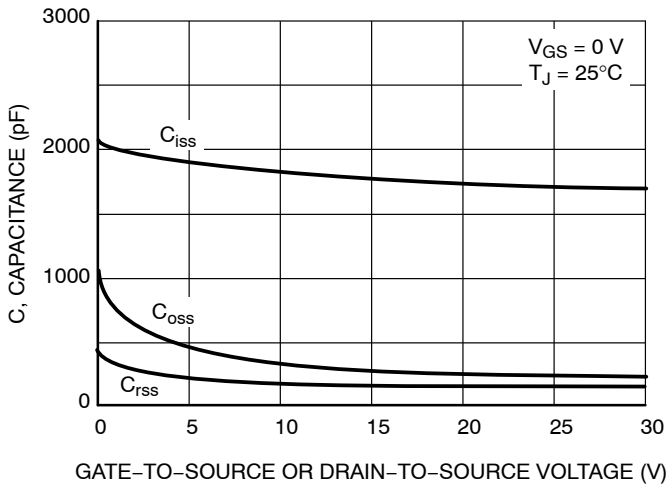
Figure 7. Capacitance Variation
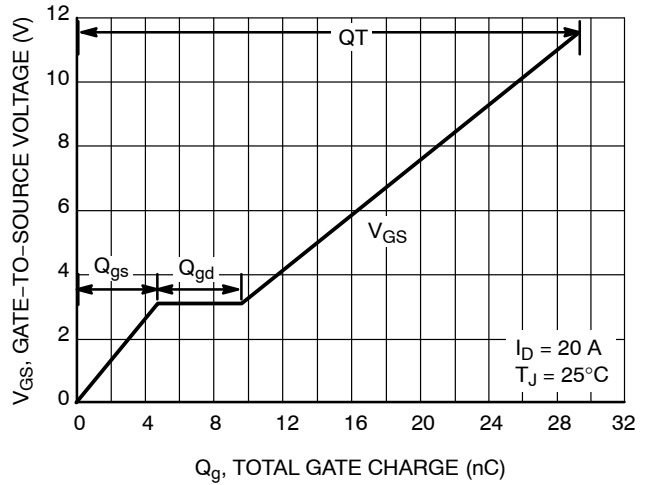
Figure 8. Gate−to−Source and
Drain−to−Source Voltage vs. Total Charge
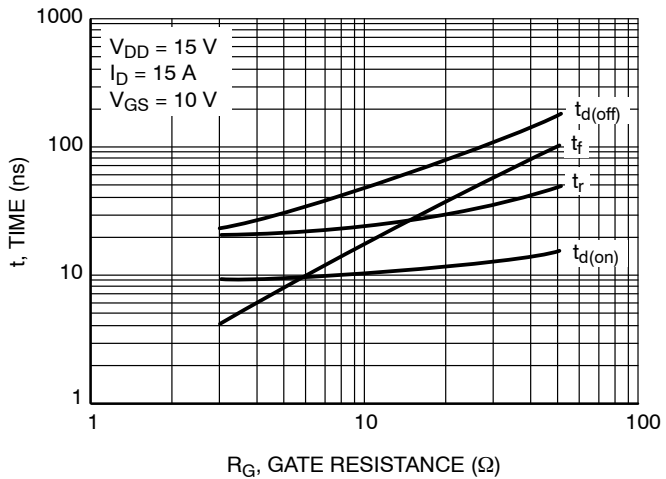
Figure 9. Resistive Switching Time Variation
vs. Gate Resistance
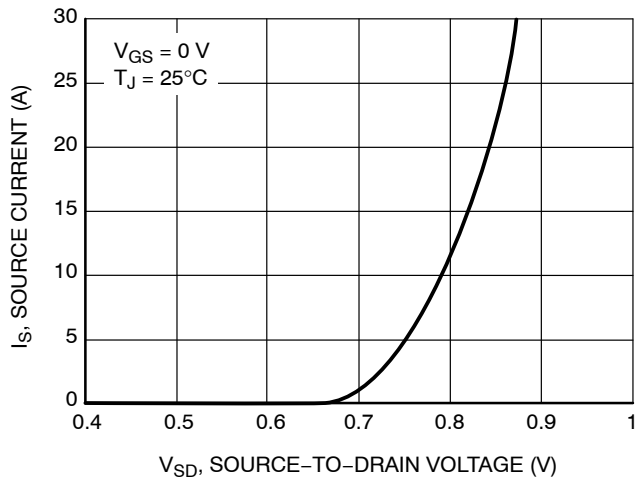
Figure 10. Diode Forward Voltage vs. Current
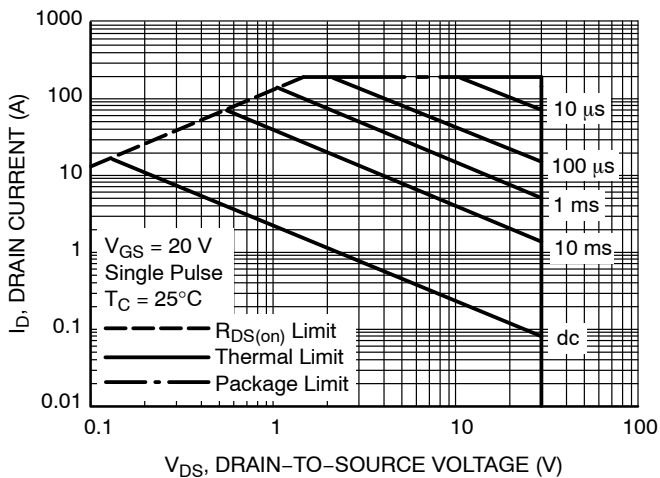
Figure 11. Maximum Rated Forward Biased
Safe Operating Area
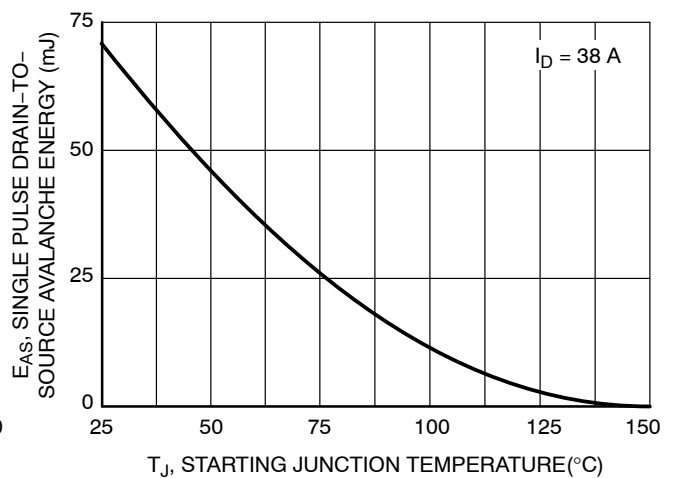
Figure 12. Maximum Avalanche Energy vs.
Starting Junction Temperature

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012

SCALE 2:1
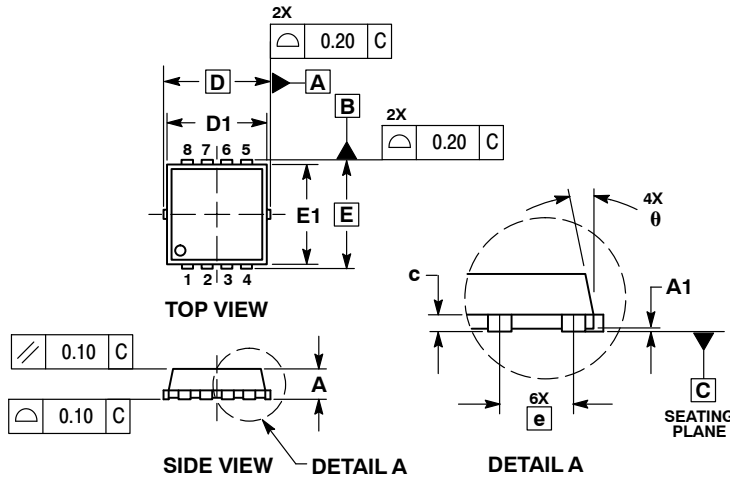
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

TOP VIEW

SIDE VIEW — **DETAIL A**

DETAIL A

SEATING PLANE

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D	3.30 BSC			0.130 BSC		
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E	3.30 BSC			0.130 BSC		
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e	0.65 BSC			0.026 BSC		
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °

BOTTOM VIEW

GENERIC MARKING DIAGRAM*

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1 ○
  XXXXX
  AYWW■
       ■
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XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
■ = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb–Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT*

DIMENSION: MILLIMETERS
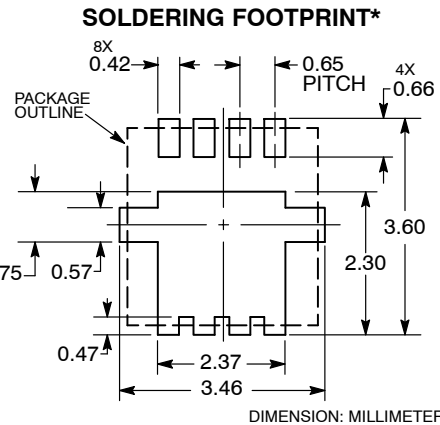
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	WDFN8 3.3X3.3, 0.65P		PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

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